



ZXTP03200BG

### 200V PNP MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

#### **Features**

- BV<sub>CEO</sub> > -200V
- I<sub>C</sub> = -2A High Continuous Collector Current
- I<sub>CM</sub> = -5A Peak Pulse Current
- Low Saturation Voltage  $V_{CE(sat)} < -160 \text{mV} @ I_C = -1 \text{A}$
- $R_{SAT} = 135m\Omega$  for a Low Equivalent On-Resistance
- · Enhanced Switching Performance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
  UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.112 grams (Approximate)

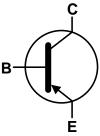
## **Applications**

• DC-DC Conversion

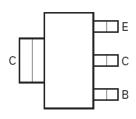




Top View



Device Symbol



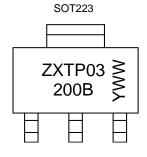
Top View Pin-Out

#### **Ordering Information** (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP03200BGTA	ZXTP03200B	7	12	1,000

- Notes:
- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



$$\begin{split} ZXTP03200B &= \text{Product Type Marking Code} \\ YWW &= \text{Date Code Marking} \\ Y \text{ or } \overline{Y} &= \text{Last Digit of Year (ex: 5= 2015)} \\ WW \text{ or } \overline{W}W &= \text{Week Code (01~53)} \end{split}$$



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-220	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-200	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ic	-2	Α
Peak Pulse Current	I <sub>CM</sub>	-5	Α
Base Current	I <sub>B</sub>	-1	Α

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1.25		
Power Dissipation	(Note 6)	D-	1.65	W	
Fower Dissipation	(Note 7)	$P_D$	3.0		
	(Note 8)		5.8		
	(Note 5)		100		
Thermal Resistance, Junction to Ambient	(Note 6)	<b>D</b>	76		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	41.6	°C/W	
	(Note 8)		21.5		
Thermal Resistance, Junction to Lead	(Note 9)	$R_{ hetaJL}$	10.5		
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C		

## ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

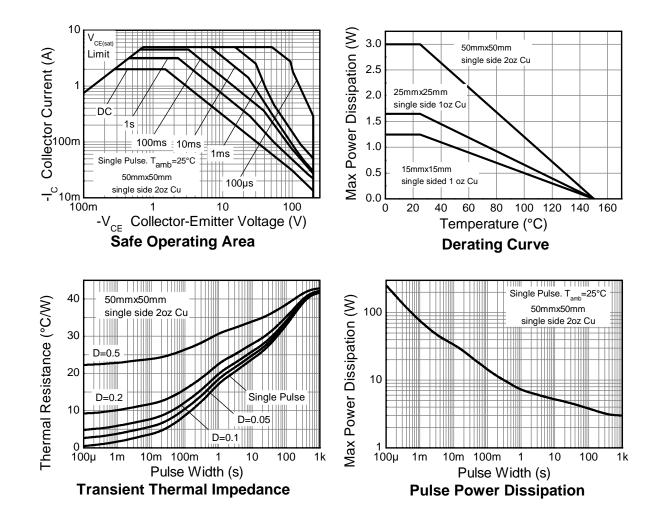
#### Notes:

- For a device mounted with the collector lead on 15mm x 15mm 1oz. copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  Same as Note 5, except the device is mounted on 25mm x 25mm 1oz. copper.
  Same as Note 5, except the device is mounted on 50mm x 50mm 2oz. copper.
  Same as Note 7, except measured at t<5 seconds.</li>
  Thermal resistance from junction to solder-point (at the end of the collector lead).

- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**





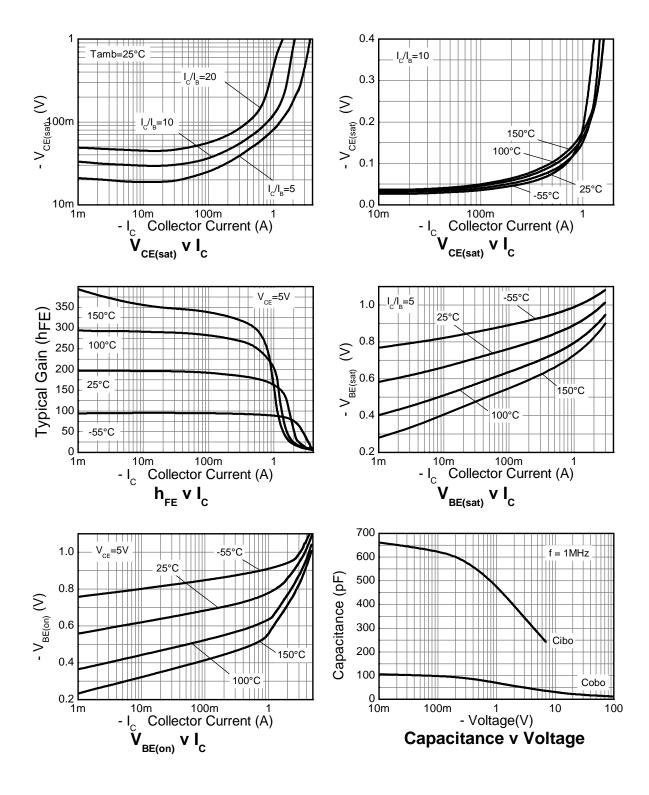
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-220	-245	-	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CER</sub>	-220	-245	-	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 11)	$BV_CEO$	-200	-225	-	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8.4	-	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I <sub>CBO</sub>	-	< -1 -	-50 -0.5	nΑ μΑ	V <sub>CB</sub> = -200V V <sub>CB</sub> = -200V, T <sub>A</sub> = +100°C
Emitter Cut-Off Current	I <sub>EBO</sub>	-	< -1	-10	nA	V <sub>EB</sub> = -6V
		100	195	-	-	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -5V
DC Current Transfer Static Patie (Note 11)	L	100	170	300		$I_C = -1A, V_{CE} = -5V$
DC Current Transfer Static Ratio (Note 11)	h <sub>FE</sub>	20	50	-		$I_C = -2A$ , $V_{CE} = -5V$
		-	5	-		$I_C = -5A$ , $V_{CE} = -5V$
	V <sub>CE(sat)</sub>	-	-37	-50	1	$I_C = -0.1A$ , $I_B = -10mA$
Collector-Emitter Saturation Voltage (Note 11)		-	-130	-155		$I_C = -0.5A$ , $I_B = -25mA$
Collector-Entitler Saturation Voltage (Note 11)		-	-135	-160		$I_C = -1A$ , $I_B = -100mA$
		-	-180	-275		$I_C = -2A$ , $I_B = -400mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	-	-955	-1,100	mV	$I_C = -2A$ , $I_B = -400mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	-	-860	-1,000	mV	$I_C = -2A$ , $V_{CE} = -5V$
Transitional Frequency (Note 11)	f <sub>T</sub>	-	105	-	MHz	$I_C = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 50 MHz
Output Capacitance	$C_{obo}$	-	31	-	pF	$V_{CB} = -10V$ , $f = 1MHz$
Delay Time	t <sub>d</sub>		21	-		
Rise Time	t <sub>r</sub>		18	-	20	$V_{CC} = -50V, I_{C} = -1A,$
Storage Time	ts	-	680	-	ns	$I_{B1} = -I_{B2} = -100 \text{mA}$
Fall Time	t <sub>f</sub>	-	75	-		

Note: 11. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



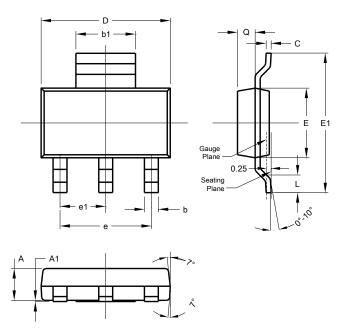
## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





## **Package Outline Dimensions**

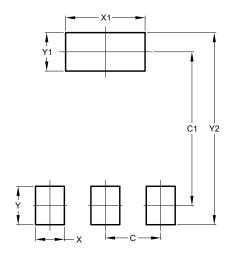
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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